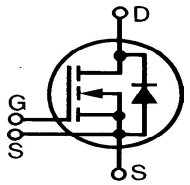
IXYS

X2-Class HiPerFET™ Power MOSFET

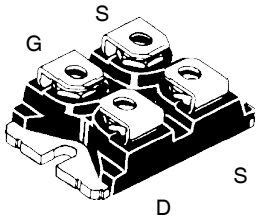
IXFN120N65X2

V_{DSS} = 650V
I_{D25} = 108A
$R_{DS(on)}$ ≤ 24mΩ

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



miniBLOC, SOT-227
E153432



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	650	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	650	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	T_C = 25°C	108	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	240	A
I_A	T_C = 25°C	15	A
E_{AS}	T_C = 25°C	3.5	J
P_D	T_C = 25°C	890	W
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	50	V/ns
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
V_{ISOL}	50/60 Hz, RMS t = 1 minute	2500	V~
	$I_{ISOL} \le$ 1mA t = 1 second	3000	V~
M_d	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
Weight		30	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	650			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA	3.5		5.0	V
I_{GSS}	V_{GS} = ± 30V, V_{DS} = 0V			± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			50	μA
	T_J = 125°C			5	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 60A, Note 1			24	mΩ

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 60A, Note 1	46	76		S
R_{Gi}	Gate Input Resistance		0.74		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		14		nF
C_{oss}			8700		pF
C_{rss}			5.5		pF
	Effective Output Capacitance				
$C_{o(er)}$	Energy related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		455		pF
$C_{o(tr)}$	Time related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		1930		pF
$t_{d(on)}$	**Resistive Switching Times**		39		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 60A		26		ns
$t_{d(off)}$	R_G = 1Ω (External)		82		ns
t_f			12		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 60A		240		nC
Q_{gs}			87		nC
Q_{gd}			65		nC
R_{thJC}				0.14	°C/W
R_{thCS}			0.05		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			120	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			480	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 60A, -di/dt = 100A/μs		220		ns
Q_{RM}	V_R = 100V, V_{GS} = 0V		2.3		μC
I_{RM}			21.0		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

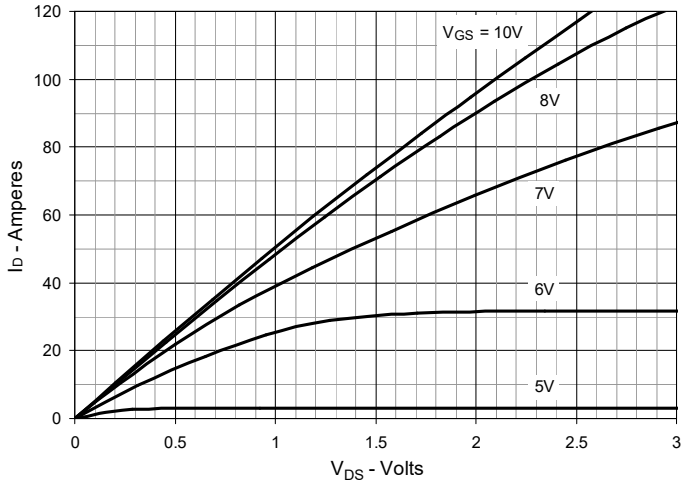


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

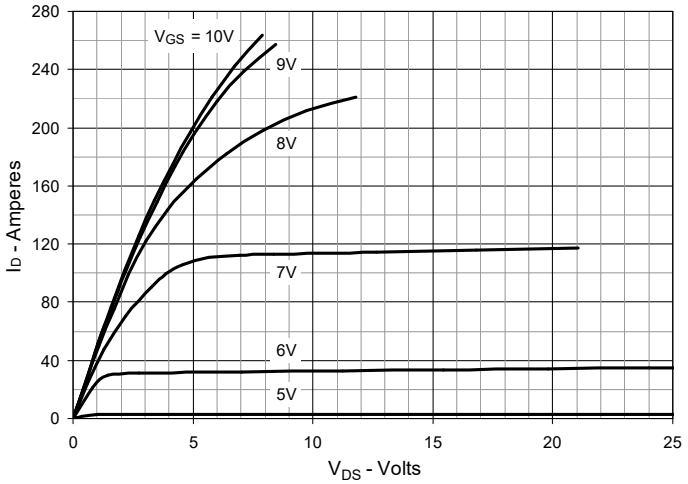


Fig. 3. Output Characteristics @ T_J = 125ºC

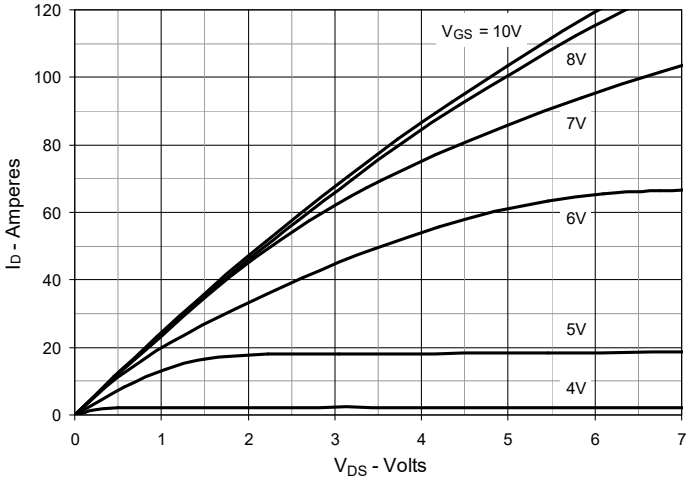


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 60A Value vs. Junction Temperature

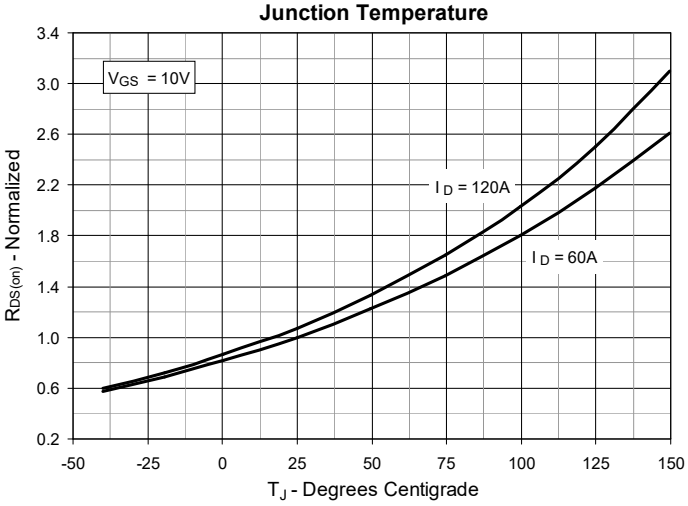


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 60A Value vs. Drain Current

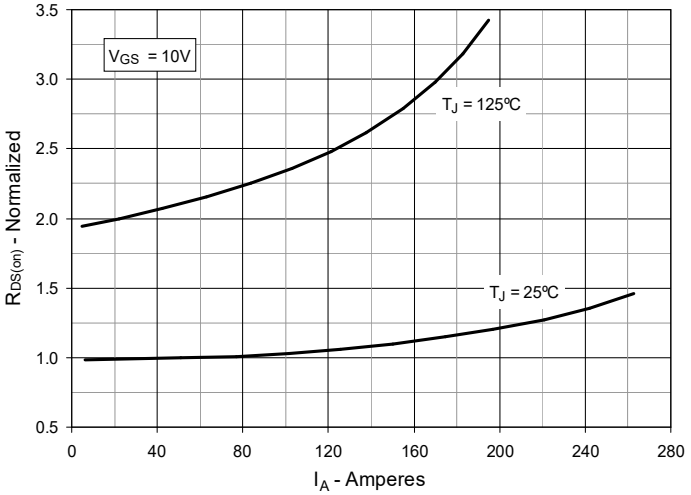
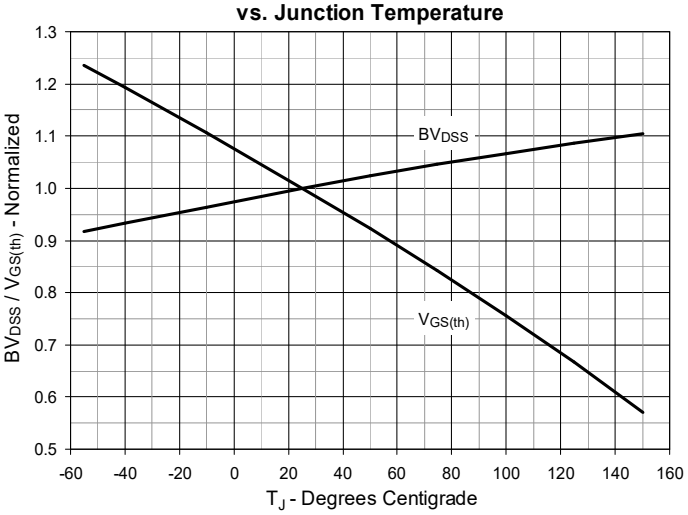


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature



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Fig. 7. Maximum Drain Current vs. Case Temperature

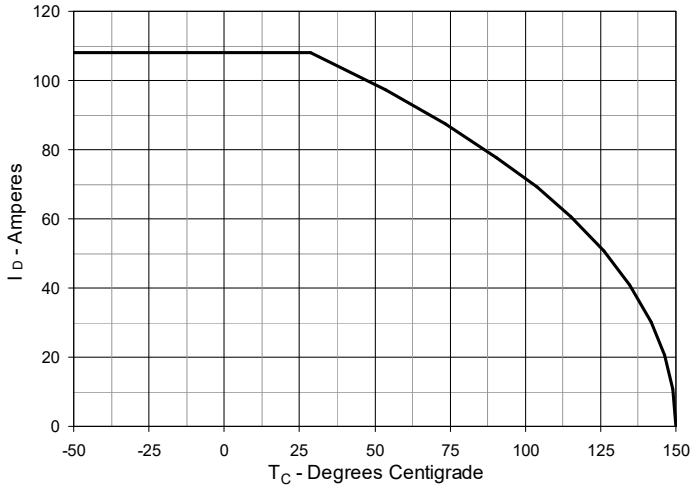


Fig. 8. Input Admittance

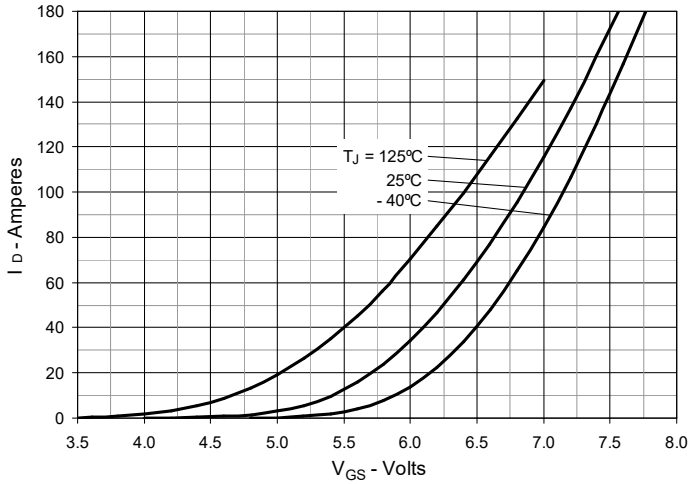


Fig. 9. Transconductance

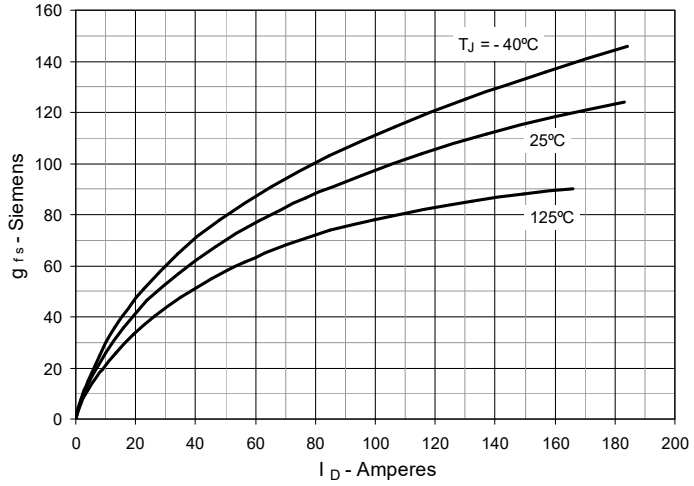


Fig. 10. Forward Voltage Drop of Intrinsic Diode

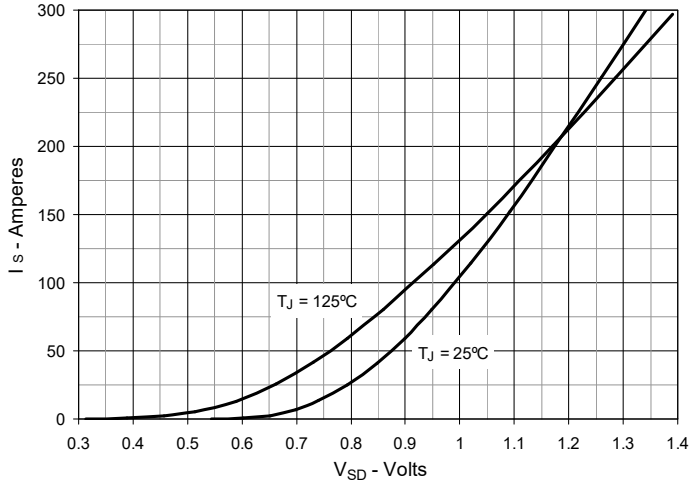


Fig. 11. Gate Charge

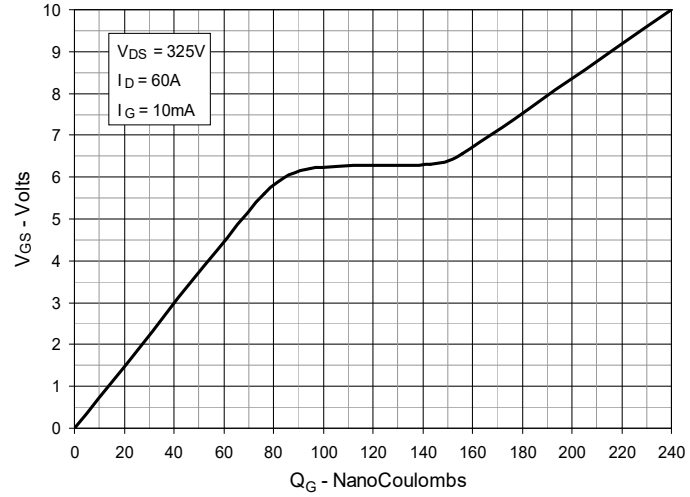
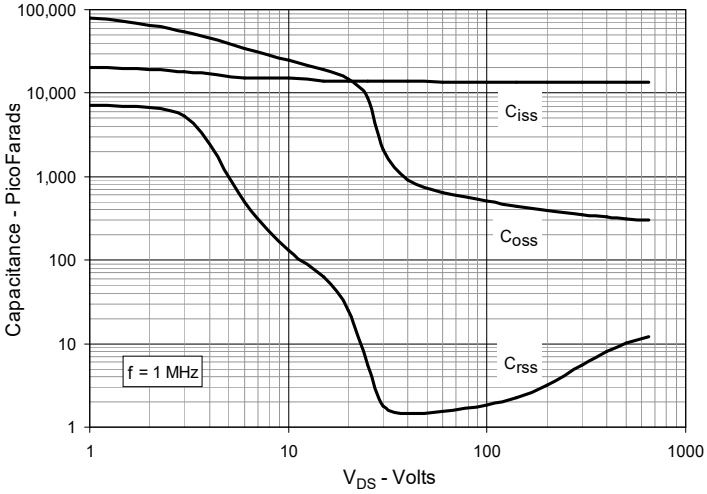


Fig. 12. Capacitance



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Fig. 13. Output Capacitance Stored Energy

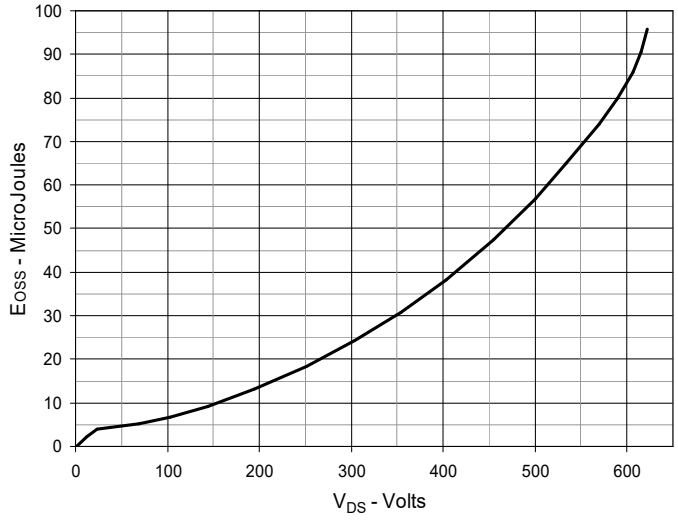


Fig. 14. Forward-Bias Safe Operating Area

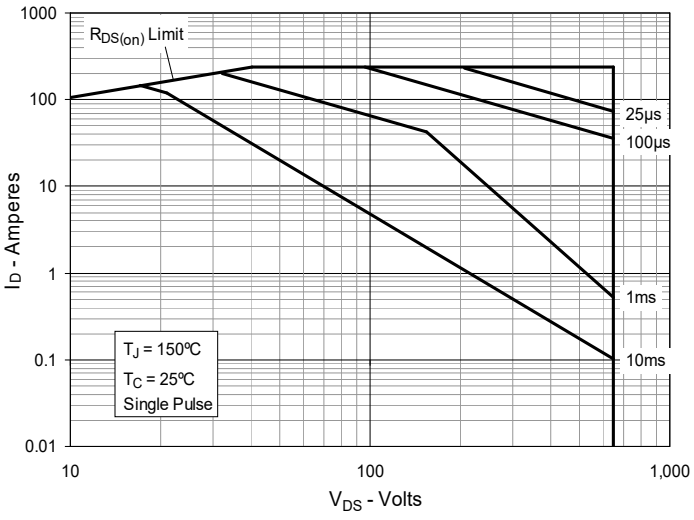
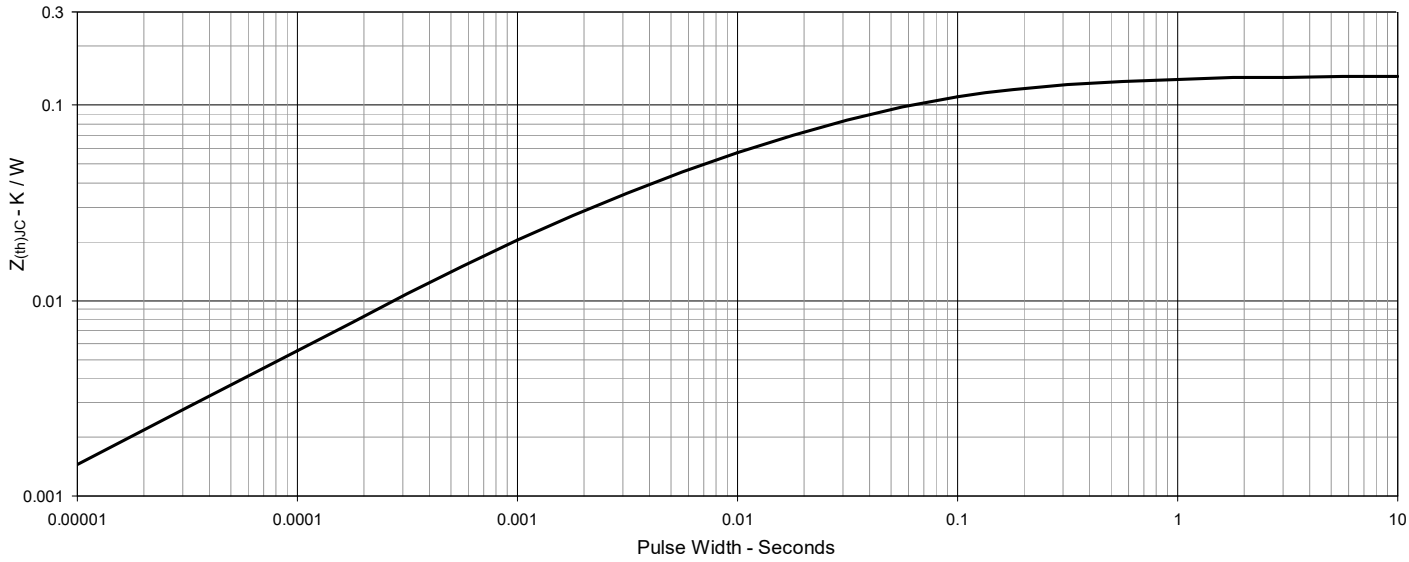
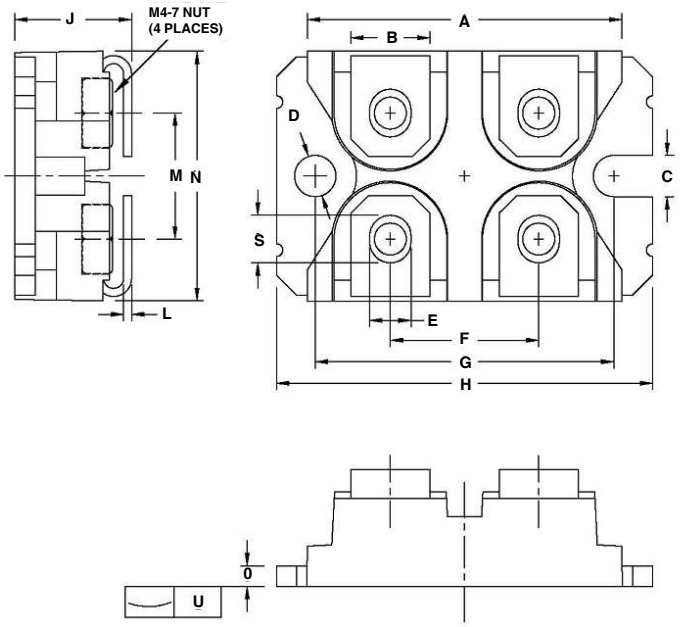


Fig. 15. Maximum Transient Thermal Impedance



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SOT-227 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

1. NUT MATERIAL:
   STANDARD – Low carbon steel with Ni plating.
   OPTIONAL: – Brass Nut is available.
   PART NUMBER–BN
2. ALL METAL SURFACE ARE PRE NI PLATED EXCEPT TRIM AREA.



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